

STARPOWER

SEMICONDUCTOR

IGBT

GD200FFX65C6SF

650V/200A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

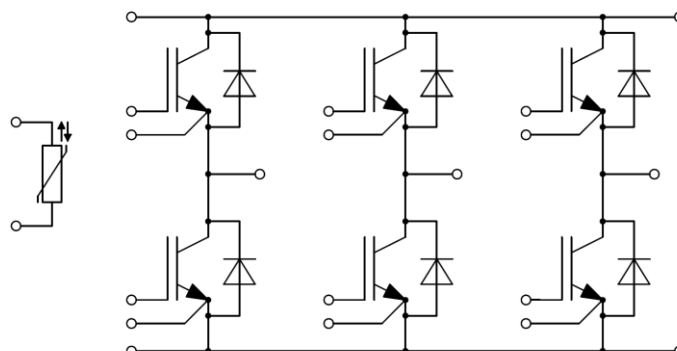
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 6 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology
- PressFIT contact technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	247	A
	@ $T_C=60^{\circ}\text{C}$	200	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	400	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	607	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	200	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	400	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.45	1.90	V	
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.60			
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		1.75			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.20\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.1	5.8	6.5	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			2.0		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		23.2		nF	
C_{res}	Reverse Transfer Capacitance			0.46		nF	
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.39		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}, R_G=2.0\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		150		ns	
t_r	Rise Time			30		ns	
$t_{d(off)}$	Turn-Off Delay Time			272		ns	
t_f	Fall Time			48		ns	
E_{on}	Turn-On Switching Loss			1.00		mJ	
E_{off}	Turn-Off Switching Loss			4.52		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=300\text{V}, I_C=200\text{A}, R_G=2.0\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		160		ns
t_r	Rise Time				40		ns
$t_{d(off)}$	Turn-Off Delay Time			296		ns	
t_f	Fall Time			56		ns	
E_{on}	Turn-On Switching Loss			1.55		mJ	
E_{off}	Turn-Off Switching Loss			5.36		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}, R_G=2.0\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			170		ns
t_r	Rise Time				40		ns
$t_{d(off)}$	Turn-Off Delay Time			304		ns	
t_f	Fall Time			56		ns	
E_{on}	Turn-On Switching Loss			1.80		mJ	
E_{off}	Turn-Off Switching Loss			5.52		mJ	
I_{SC}	SC Data		$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 650\text{V}$		1000		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.55	2.00	V
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.50		
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.45		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=200\text{A},$ $-di/dt=5700\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		10.0		μC
I_{RM}	Peak Reverse Recovery Current			160		A
E_{rec}	Reverse Recovery Energy			3.00		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=200\text{A},$ $-di/dt=5700\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		17.0		μC
I_{RM}	Peak Reverse Recovery Current			230		A
E_{rec}	Reverse Recovery Energy			5.20		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=200\text{A},$ $-di/dt=5700\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		20.0		μC
I_{RM}	Peak Reverse Recovery Current			240		A
E_{rec}	Reverse Recovery Energy			5.80		mJ

NTC Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_C=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$		3433		K

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		21		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		1.80		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.247	K/W
	Junction-to-Case (per Diode)			0.445	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.084		K/W
	Case-to-Heatsink (per Diode)		0.151		
	Case-to-Heatsink (per Module)		0.009		
M	Mounting Screw:M5	3.0		6.0	N.m
G	Weight of Module		300		g

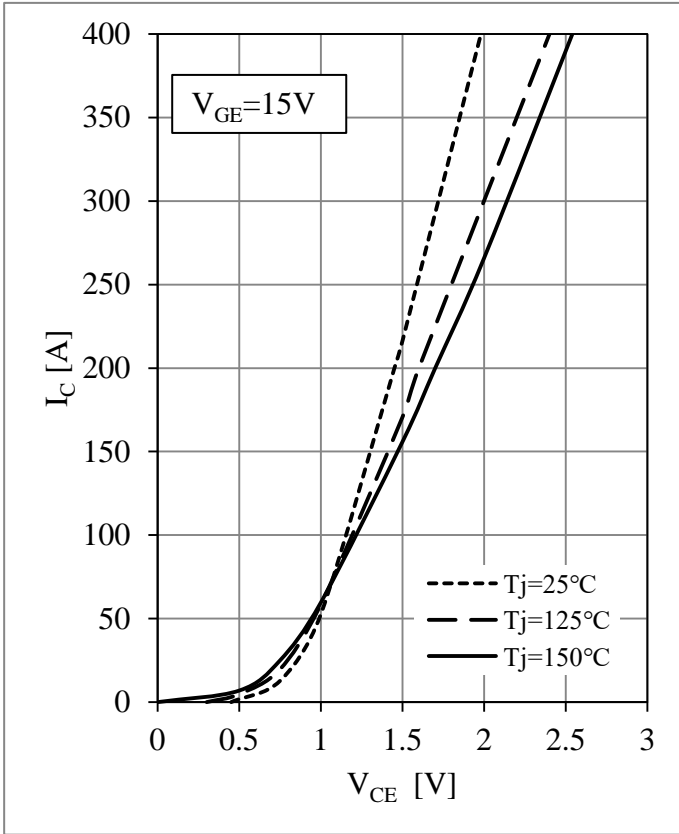


Fig 1. IGBT Output Characteristics

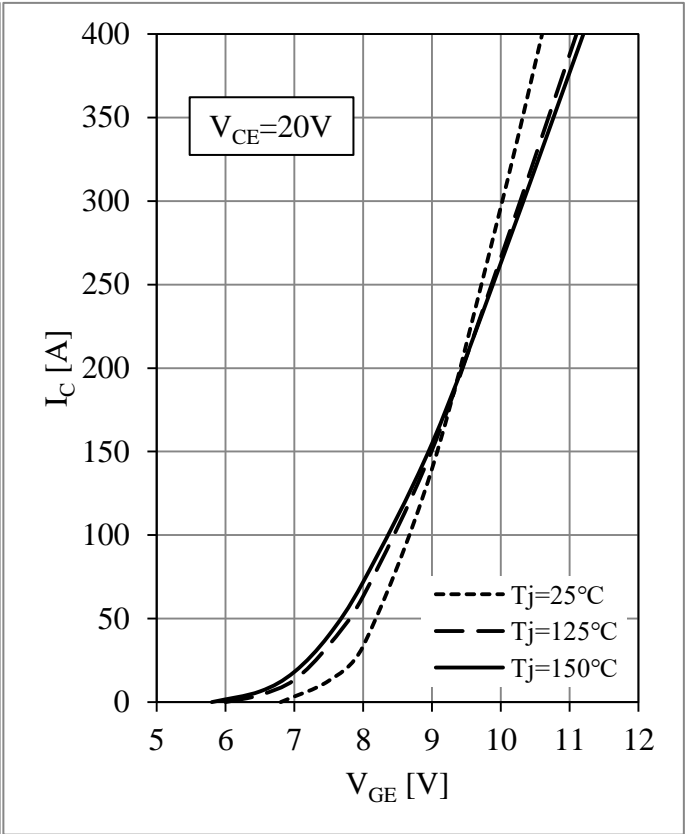


Fig 2. IGBT Transfer Characteristics

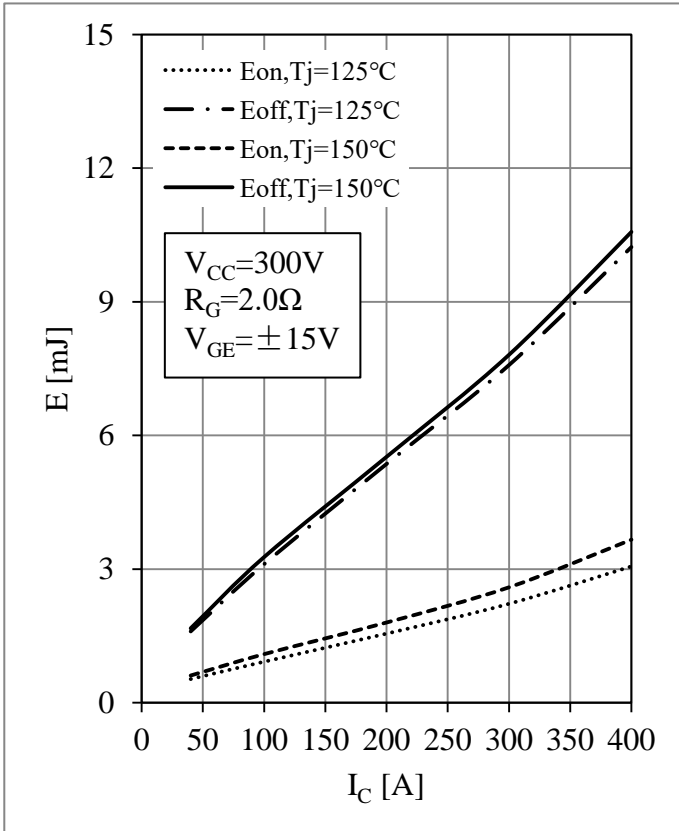


Fig 3. IGBT Switching Loss vs. I_C

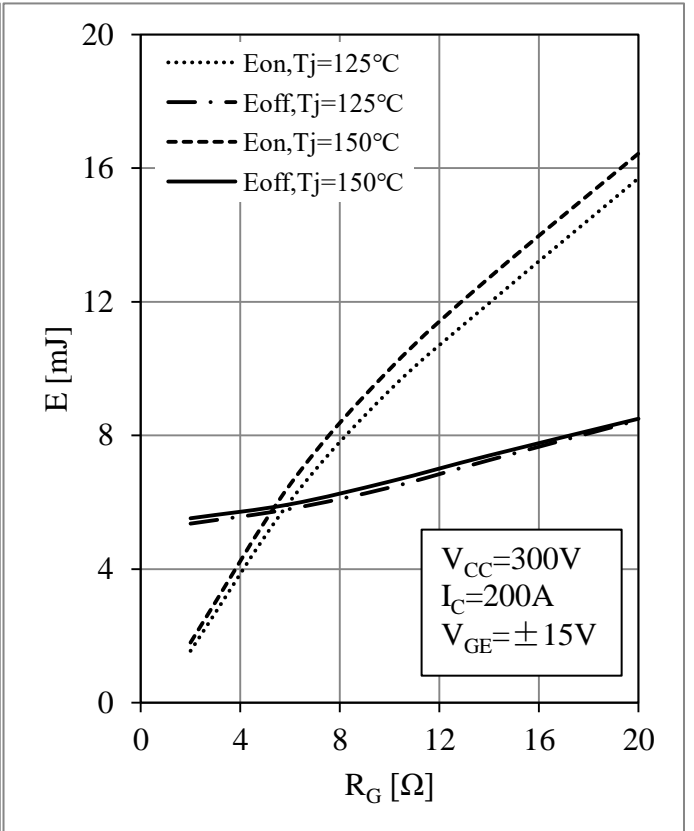


Fig 4. IGBT Switching Loss vs. R_G

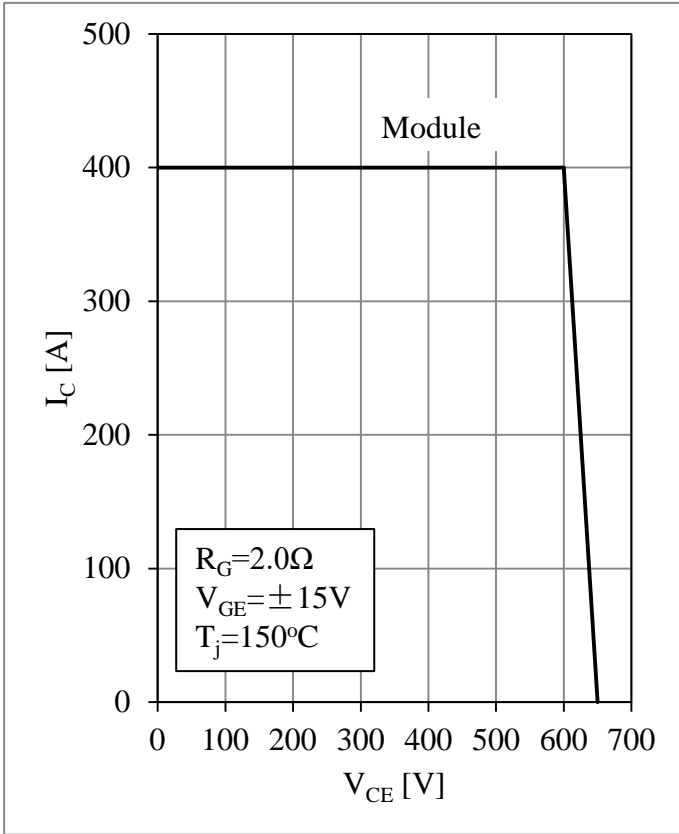


Fig 5. IGBT RBSOA

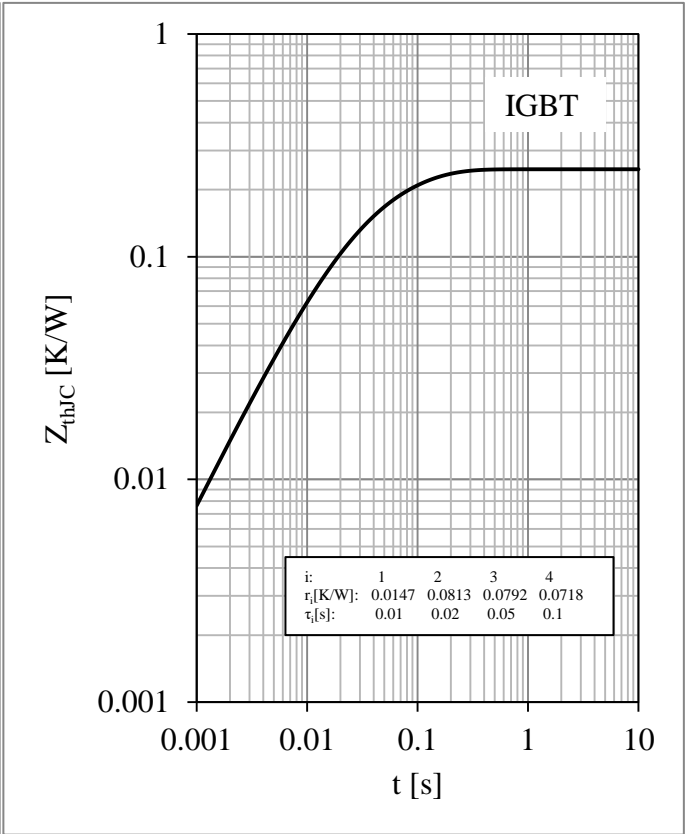


Fig 6. IGBT Transient Thermal Impedance

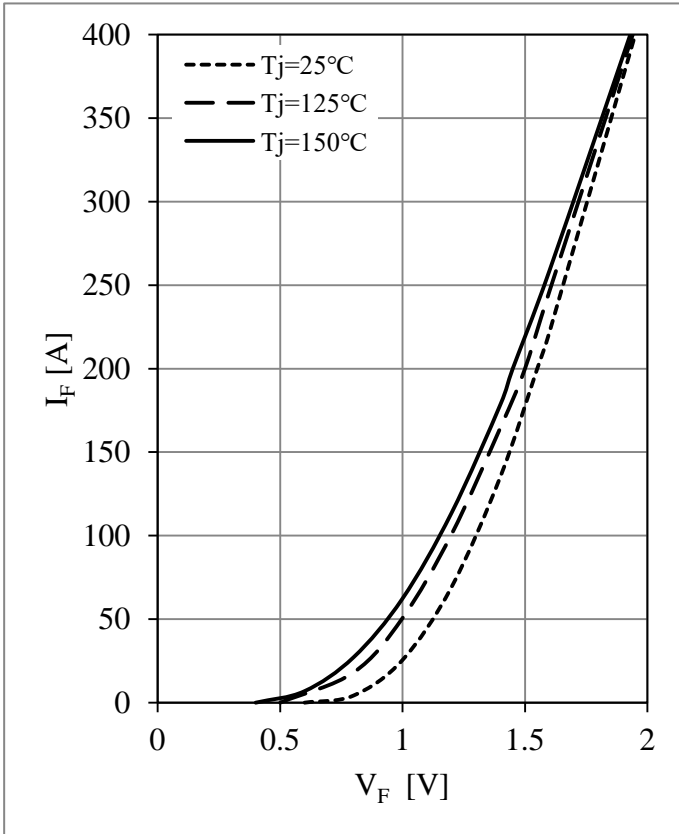


Fig 7. Diode Forward Characteristics

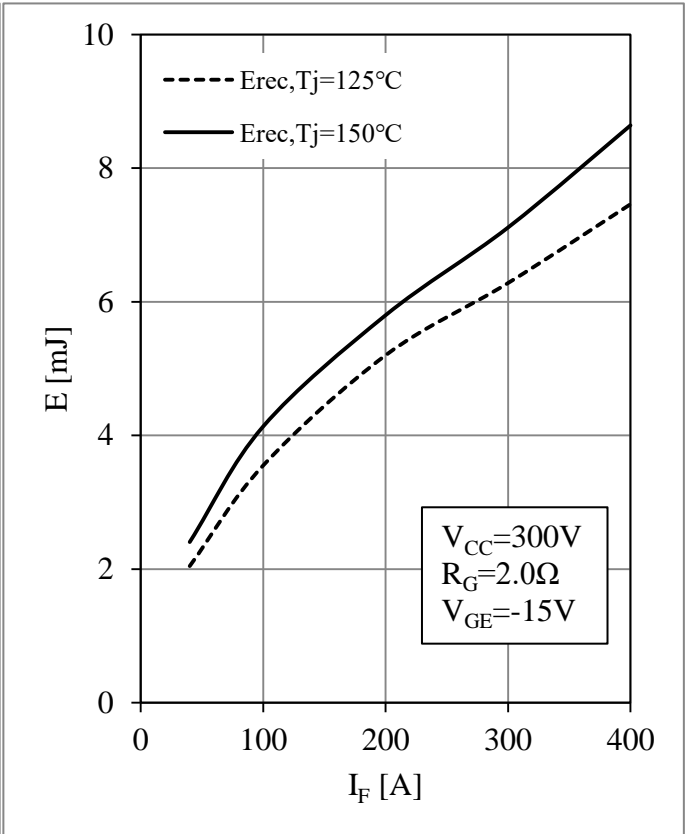


Fig 8. Diode Switching Loss vs. I_F

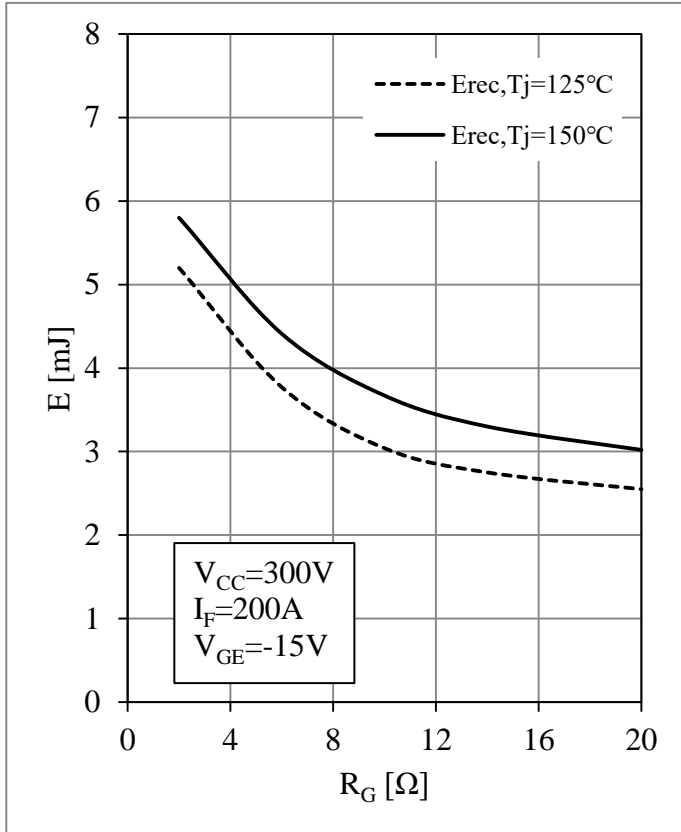


Fig 9. Diode Switching Loss vs. R_G

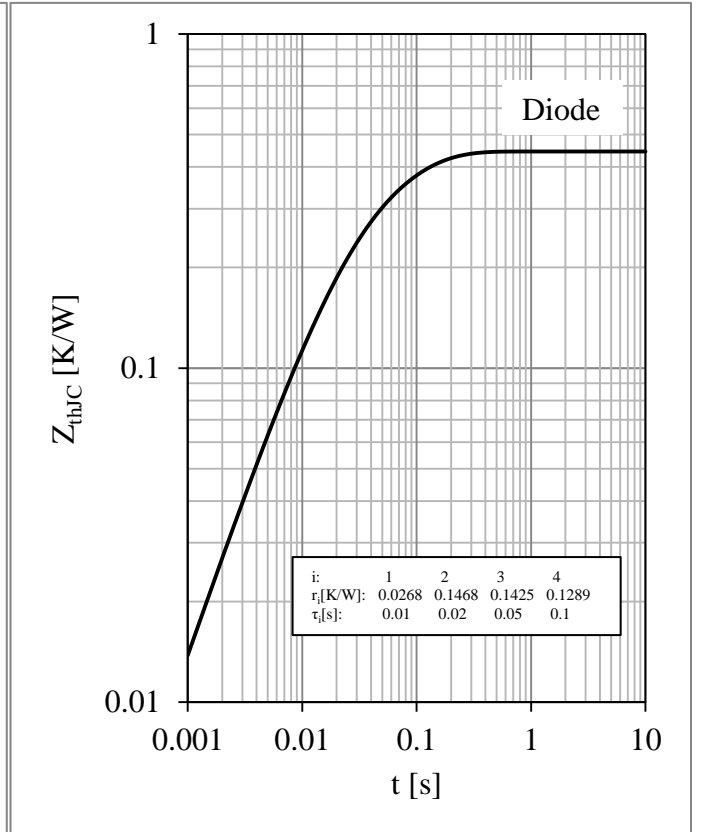


Fig 10. Diode Transient Thermal Impedance

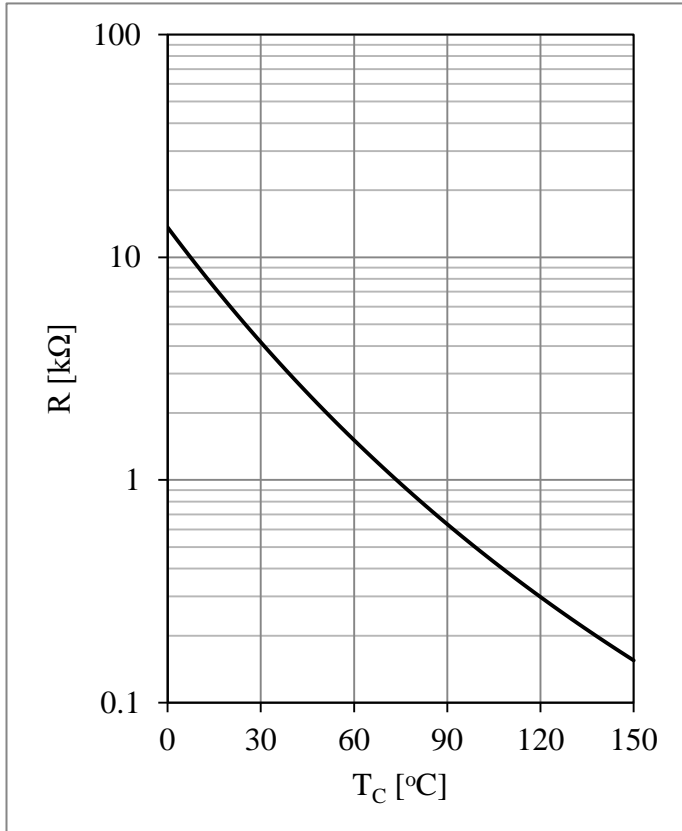
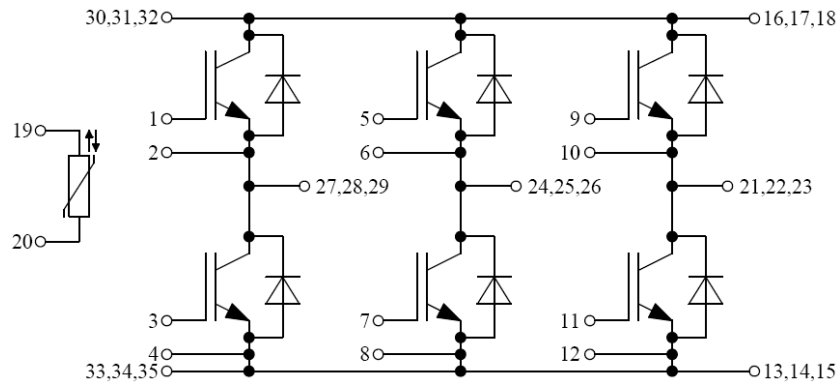


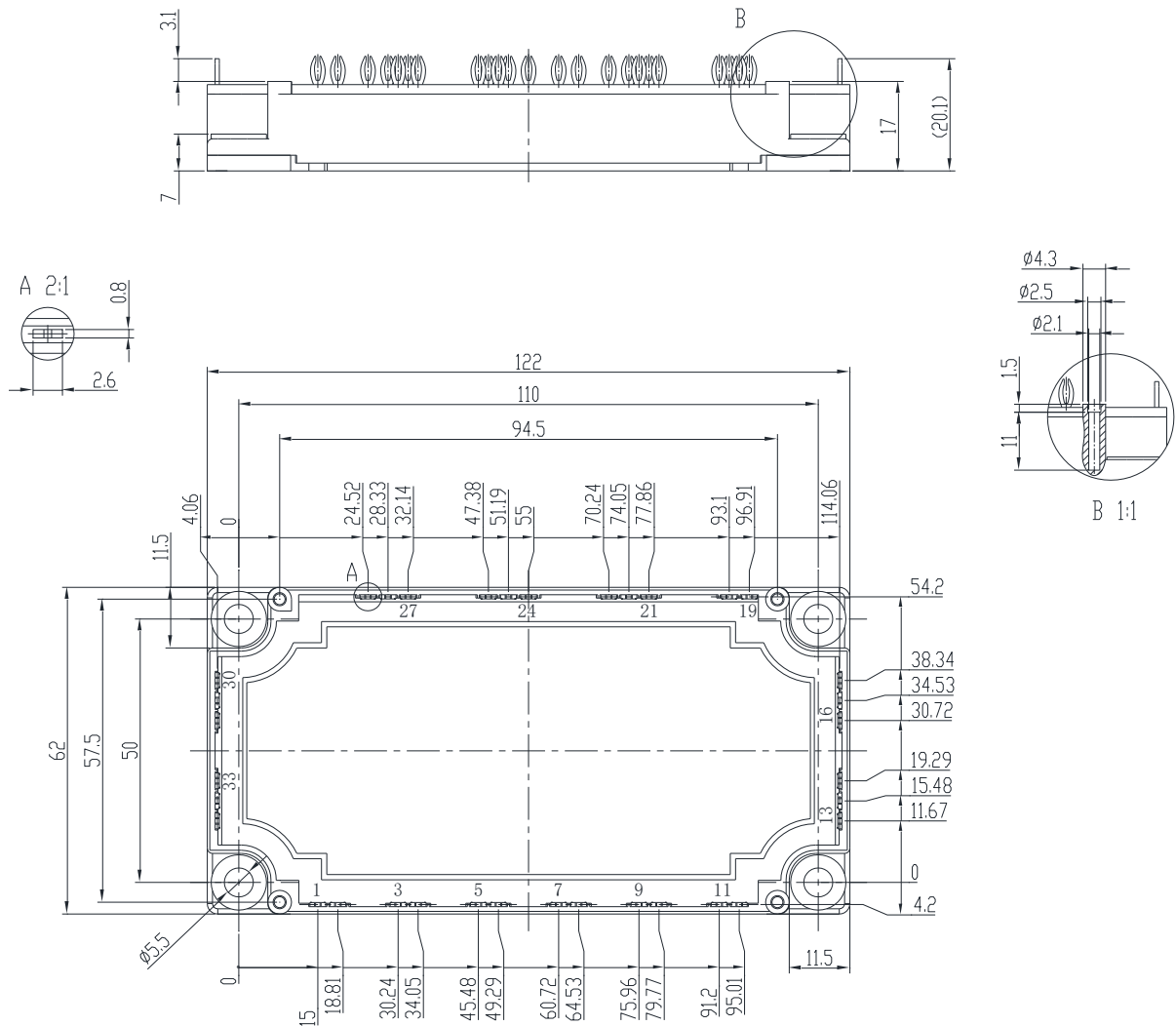
Fig 11. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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